## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

n re Patent Application of Confirmation No. 7689

YAMAGATA et al. Allowed: January 2, 2004

Serial No. 09/993,890 Atty Ref.: 925-219

Filed: November 27, 2001 Group: 2825

For: METHOD FOR MANUFACTURING Examiner: Lee, Calvin

NONVOLATILE SEMICONDUCTOR MEMORY WITH NARROW VARIATION IN THRESHOLD

VOLTAGES OF MEMORY CELLS

\* \* \* \* \* \* \* \* \* \* \*

March 29, 2004

Mail Stop: Issue Fee Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

## COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Sir:

The instant application was allowed January 2, 2004. However, the Reasons for Allowance are not commensurate with the scope of the claims.

For example, and without limitation, claims 1 and 5 do not require "thermally oxidizing the sidewall of a floating gate."

Please let me know if you should have any questions.

**YAMAGATA** et al. Serial No. 0**3**/993,890

Respectfully submitted,

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